Amendments to the Specification

In the Abstract, please amend the following:

~~The invention relates to the manufacturing of a bipolar transistor device (10) in which the emitter is formed using a polycrystalline silicon region (14) which is present in a window in an insulating layer (13) and which extends laterally over said insulating layer (13). The silicon region (14) as well as another silicon region (12) bordering the stack of insulating region (13) and silicon region (14) are silicided by means of a metal layer (16) deposited over the structure. The sideface of the stack is provided with means to avoid bridging of the silicides (17) to be formed.~~

~~According to the invention the means to prevent bridging of the silicides to be formed comprises that the side face of the stack is structured in such a way that the distance between the upper surface of the silicon region (14) and the upper surface the other silicon region (12) along the surface of the side face of the stack is made longer than the total thickness of the insulating layer (13) and the semiconductor layer (14). Through the increased path by either a positive or negative slope of the side face of the stack, the bridging of silicides is avoided.~~

~~Preferred embodiments relate to how the side face of the stack is structured.~~

~~Fig. 7~~

The invention relates to the manufacturing of a bipolar transistor device in which the emitter is formed using a polycrystalline silicon region which is present in a window in an insulating layer and which extends laterally over said insulating layer. Consistent with an example embodiment, the preventing of bridging of silicides to be formed comprises that the side face of the stack is structured in such a way that the distance between the upper surface of the silicon region and the upper surface the other silicon region along the surface of the side face of the stack is made longer than the total thickness of the insulating layer and the semiconductor layer. Through the increased path by either a positive or negative slope of the side face of the stack, the bridging of silicides is avoided.